

N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

The HM10N10K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

GENERAL FEATURES

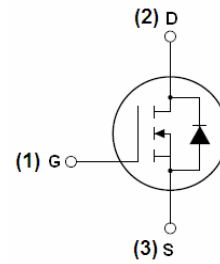
- $V_{DS} = 100V, I_D = 9.6A$
 $R_{DS(ON)} < 130m\Omega @ V_{GS} = 10V$ (Typ: 105m Ω)
- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

100% UIS TESTED!

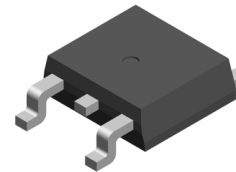
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin Assignment



TO-252-2L top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM10N10K	HM10N10K	TO-252-2L	-	-	-

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	9.6	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	6.5	A
Pulsed Drain Current	I_{DM}	58	A
Maximum Power Dissipation	P_D	30	W
Derating factor		0.24	W/°C
Single pulse avalanche energy (Note 5)	E_{AS}	150	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JC}$	4.17	$^{\circ}\text{C/W}$
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Electrical Characteristics (TC=25 $^{\circ}\text{C}$ unless otherwise noted)

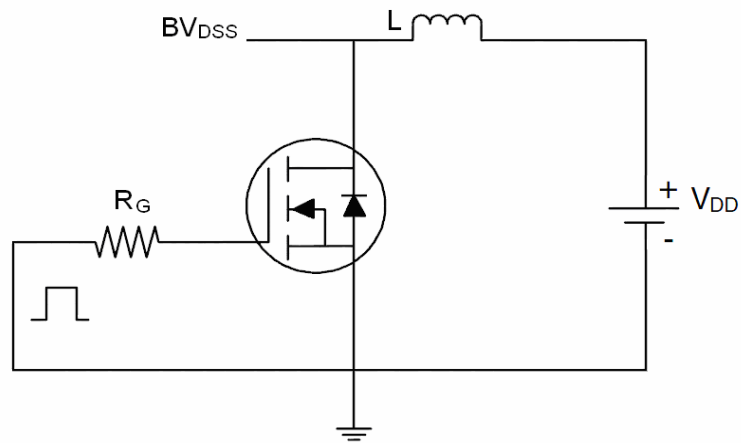
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	105	140	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =6A	3.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	690	-	PF
Output Capacitance	C _{OSS}		-	120	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =2A, R _L =15Ω V _{GS} =10V, R _G =2.5Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	7.4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	35	-	nS
Turn-Off Fall Time	t _f		-	9.1	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =3A, V _{GS} =10V	-	15.5		nC
Gate-Source Charge	Q _{gs}		-	3.2	-	nC
Gate-Drain Charge	Q _{gd}		-	4.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =9A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	9.6	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =6A di/dt = 100A/μs(Note3)	-	21		nS
Reverse Recovery Charge	Q _{rr}		-	97		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

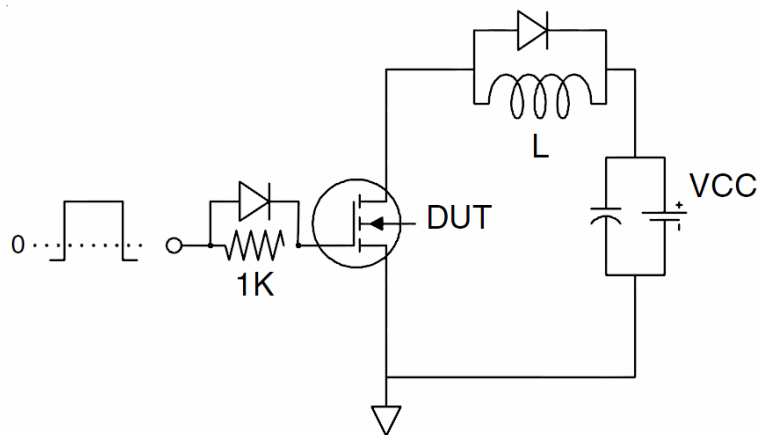
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

Test circuit

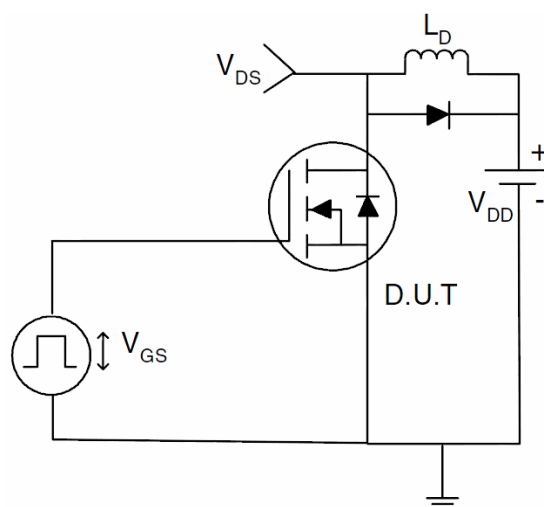
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit :



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

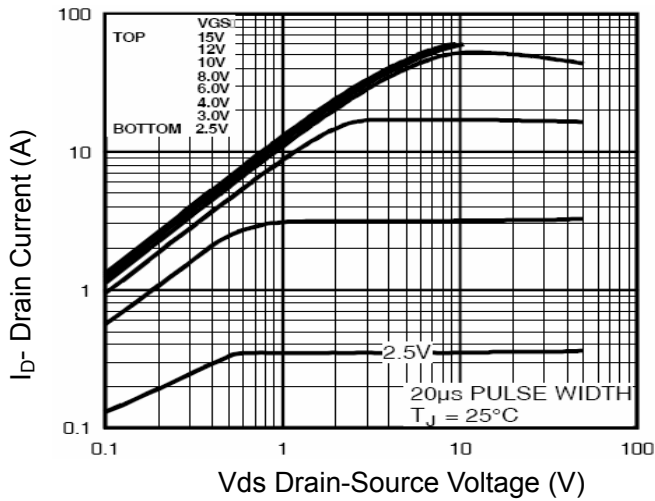


Figure 1 Output Characteristics

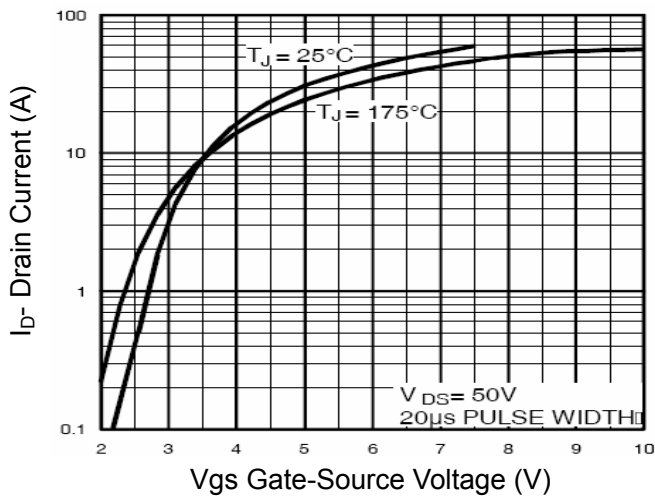


Figure 2 Transfer Characteristics

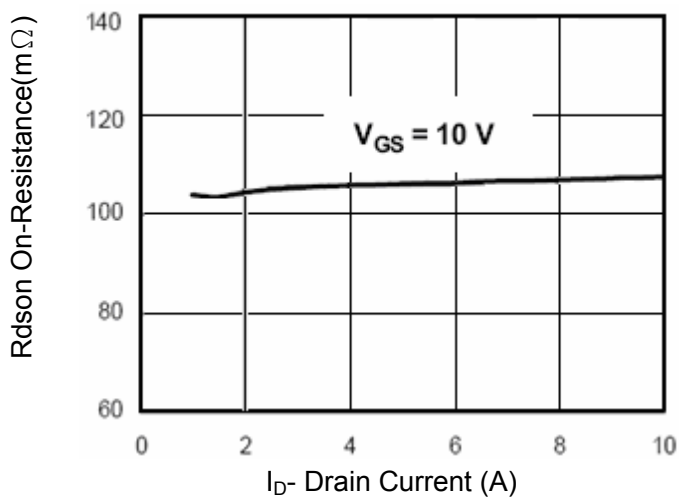


Figure 3 Rdson- Drain Current

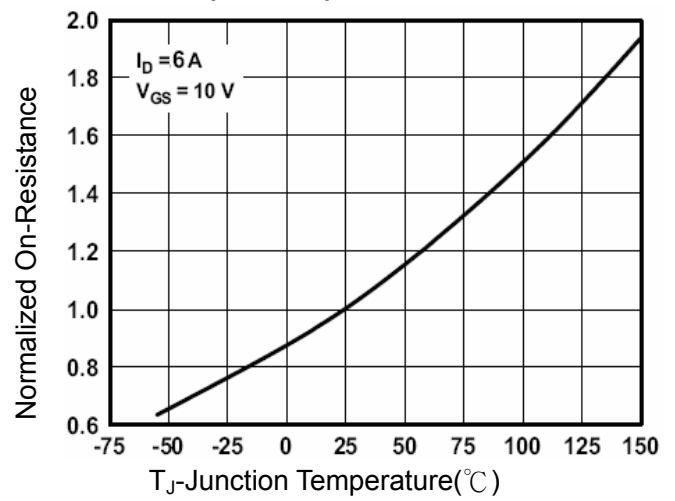


Figure 4 Rdson-Junction Temperature

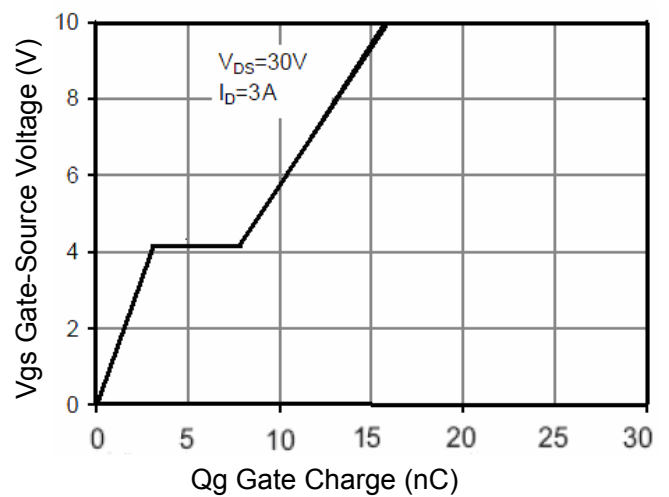


Figure 5 Gate Charge

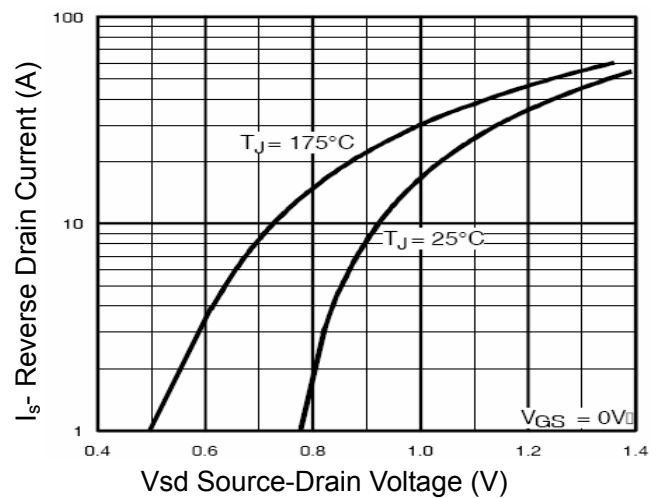


Figure 6 Source- Drain Diode Forward

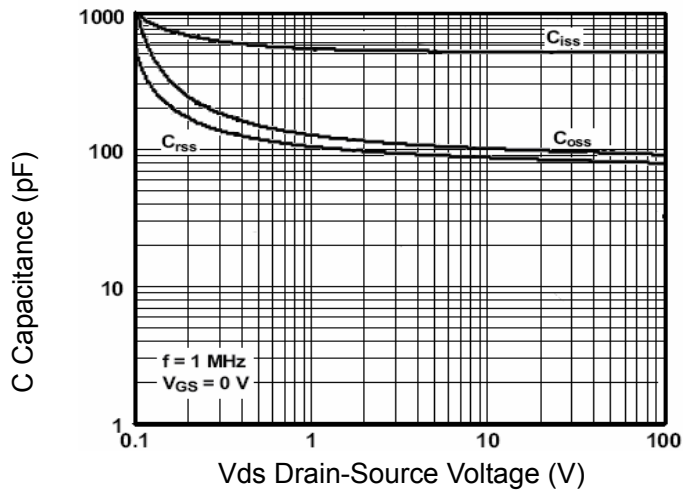


Figure 7 Capacitance vs V_{ds}

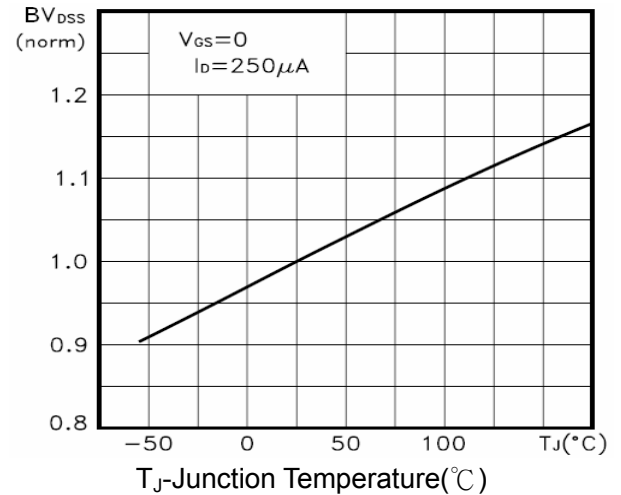


Figure 9 BV_{DSS} vs Junction Temperature

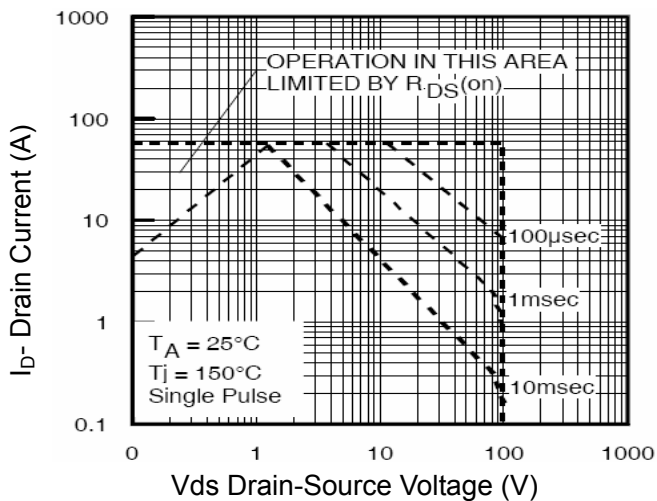


Figure 8 Safe Operation Area

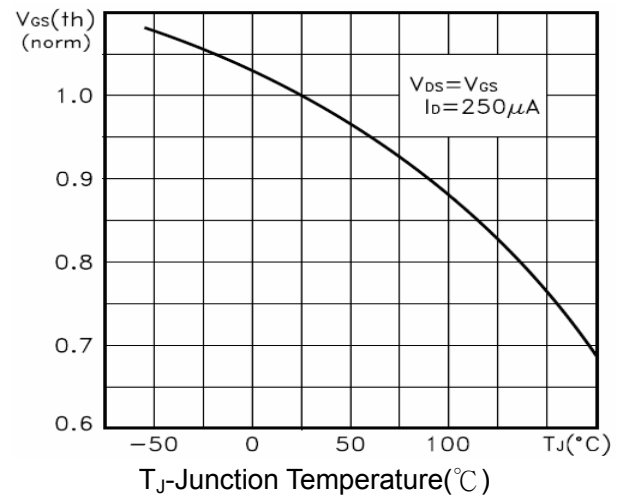


Figure 10 $V_{GS(th)}$ vs Junction Temperature

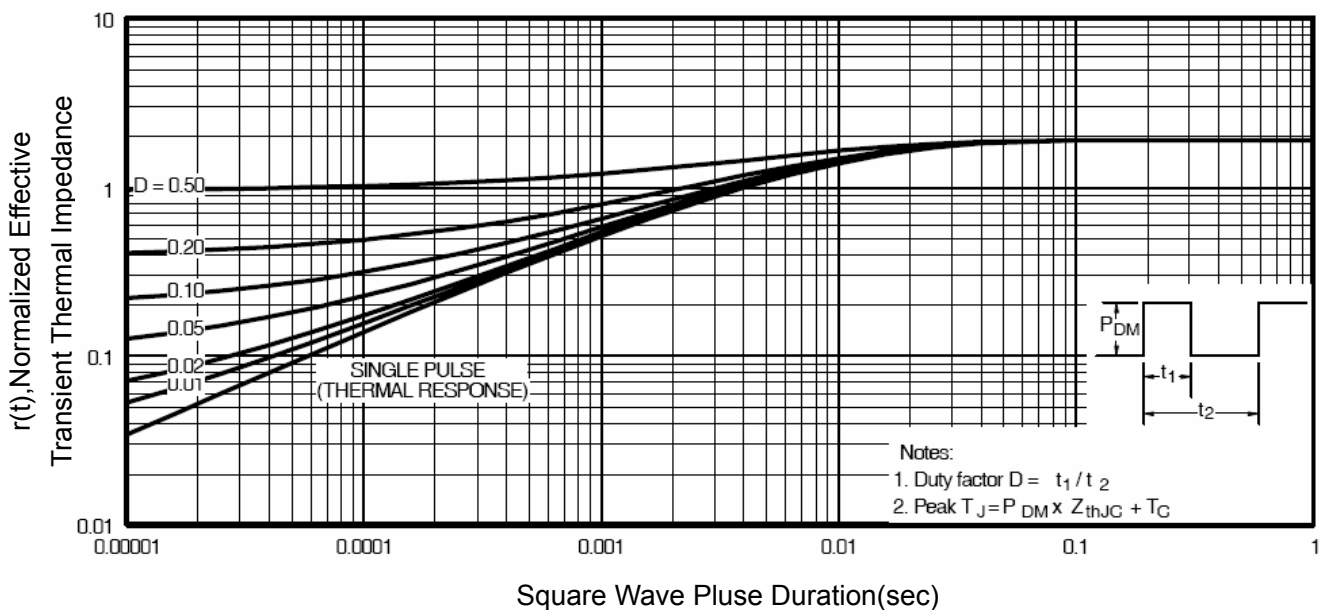
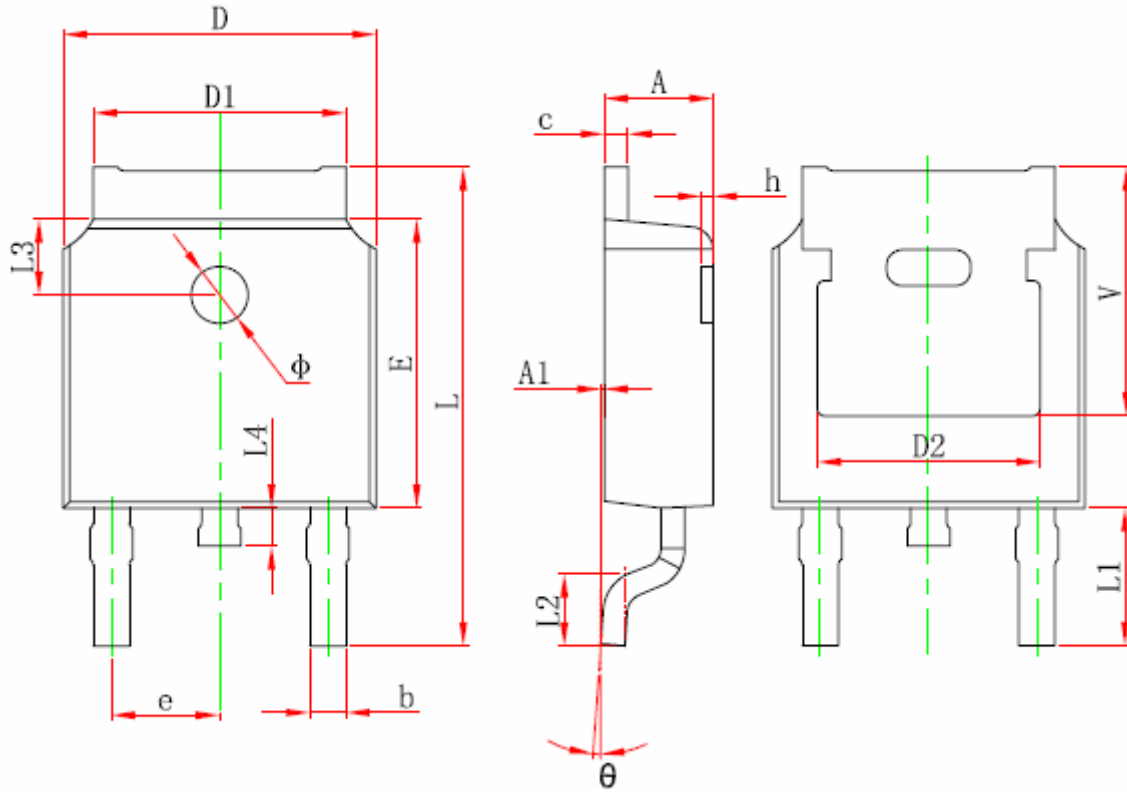


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	